

Types of Capacitors

Aluminum Electrolytics

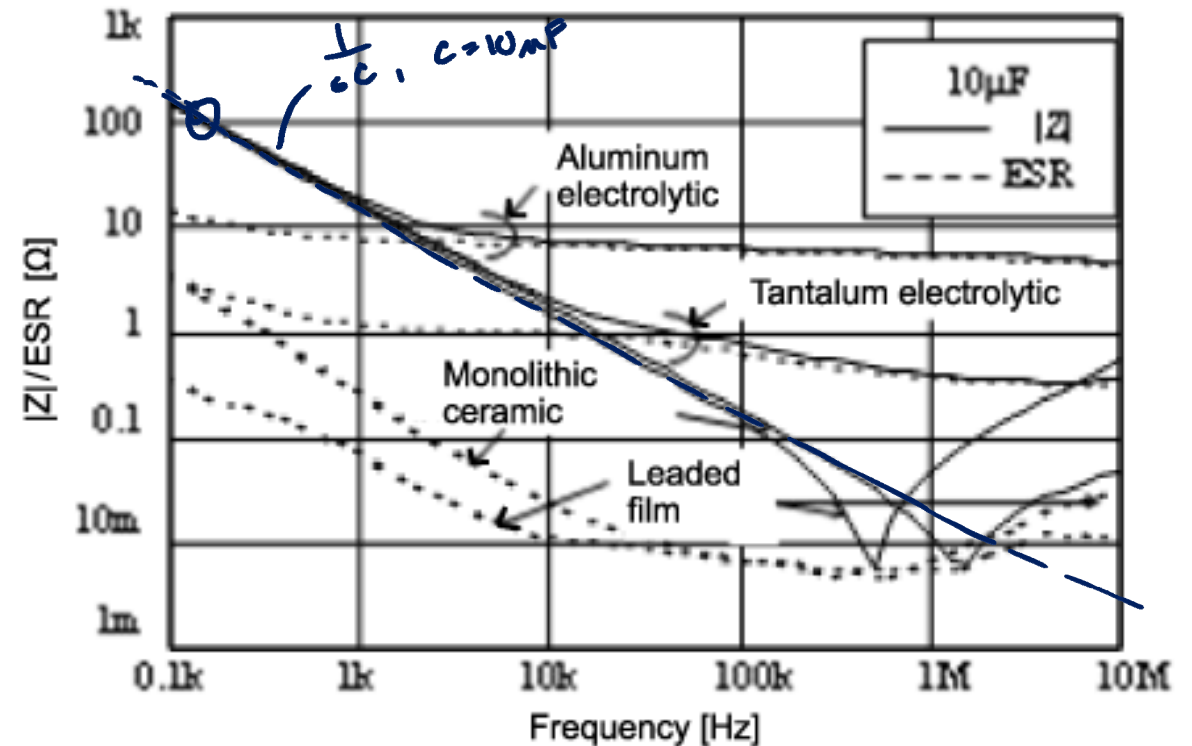
- High Capacitance density
- High ESR & ESL

Tantalum Electrolytes

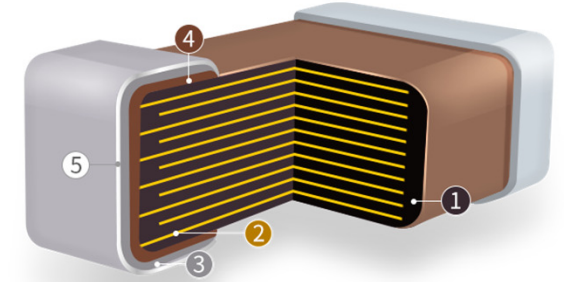
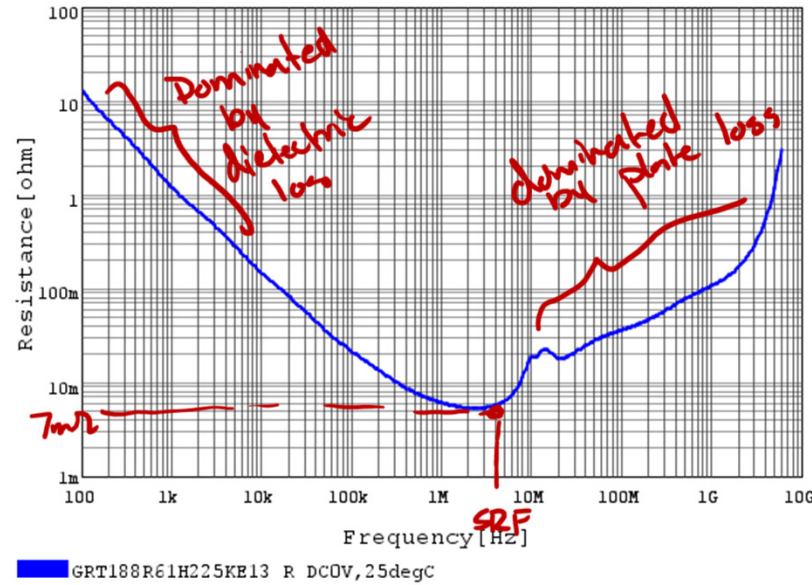
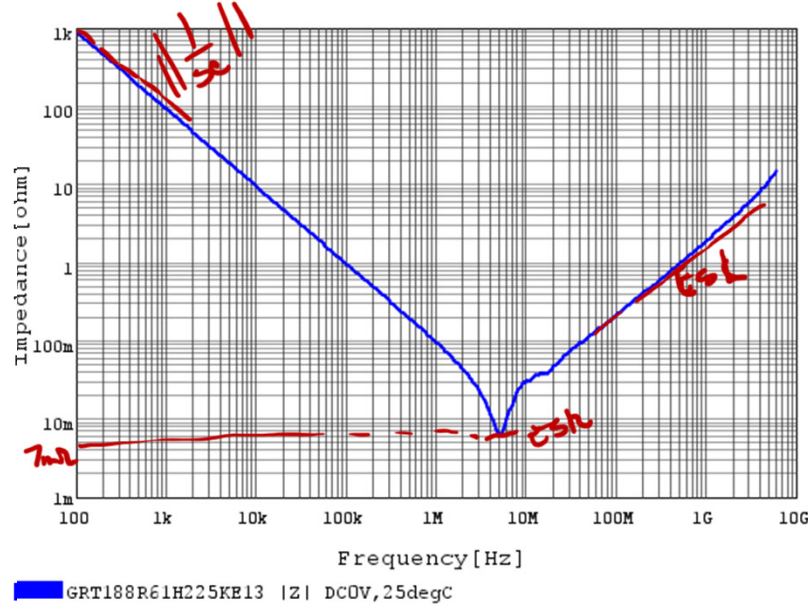
- slightly better ESR/ESL

Ceramic / Film

- low ESR/ESL
- low capacitance density compared to electrolytes



Ceramic Capacitor Impedance and Resistance

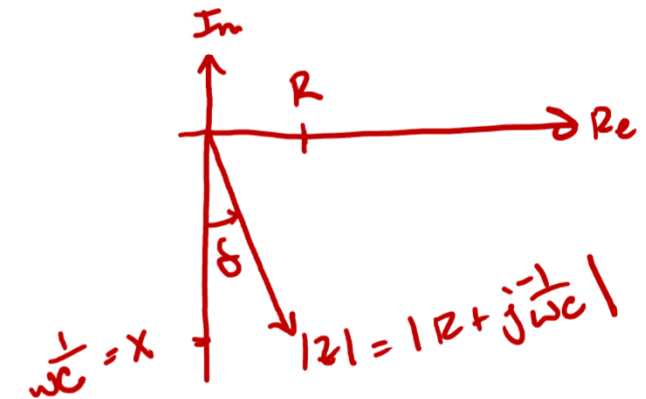


- ① Ceramic body ② Electrode (Ni/Cu*) ③ Plating (Ni)
- ④ Termination (Cu or Cu+Metal Epoxy) ⑤ Plating (Sn)

* Internal Cu electrode is only applied to limited products.
<https://m.samsungsem.com/global/product/passive-component/mlcc.do>



$$\tan \delta = DF$$



Capacitor data sources

- Murata Simsurfing
- TDK SEAT

MLCC

- Capacitor codes, e.g. X7R or C0G standardized to define stability over temperature

- **Class-II:** Codes begin with X, Y, or Z (e.g. X7R, Y5V)

- High capacitance

- Poor capacitance linearity over temperature & voltage

50V, 0603

X5R, 47nF

-55°C - 85°C

- **Class-I:** Codes begin with [CBLAMPRSTVU] (e.g. C0G, NPO)

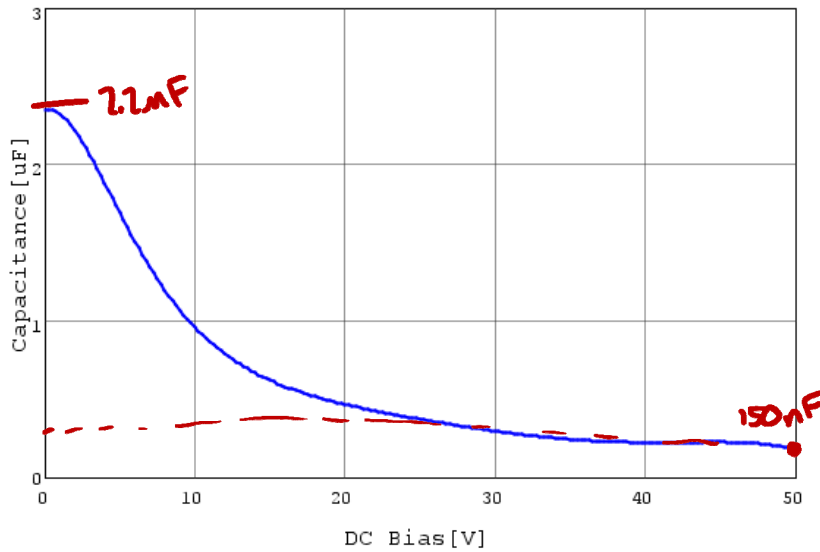
- lower capacitance

- Good capacitance linearity

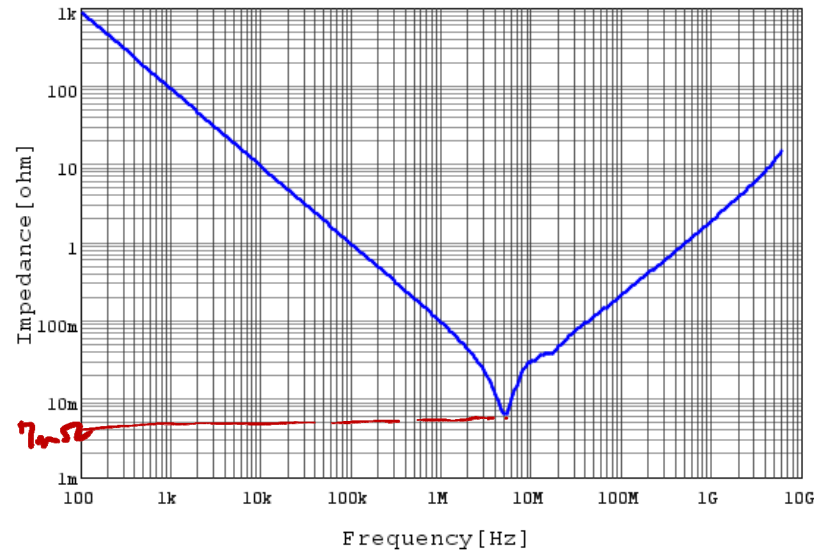
C0G, 18nF

-55°C - 125°C

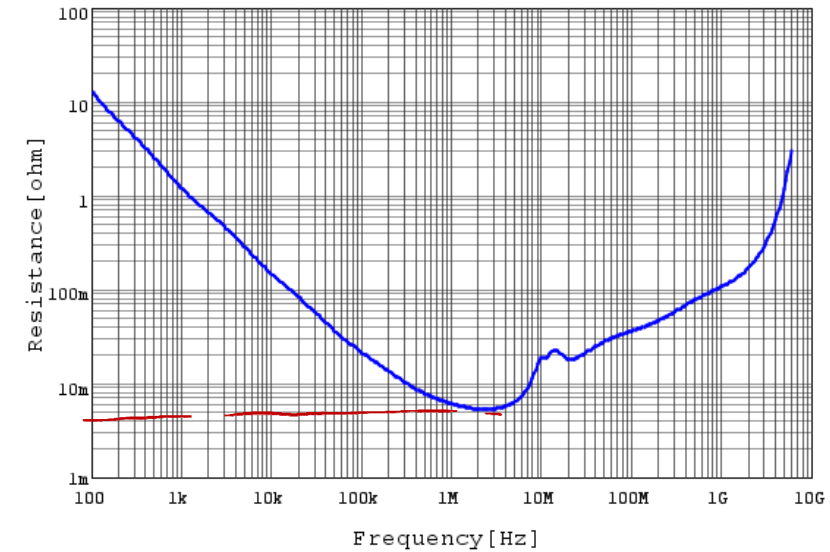
2.2 μ F, 50V X7R (Class-II) 0603 footprint



GRT188R61H225KE13 C-DC bias capacitance, 25.0degC, AC1Vrms



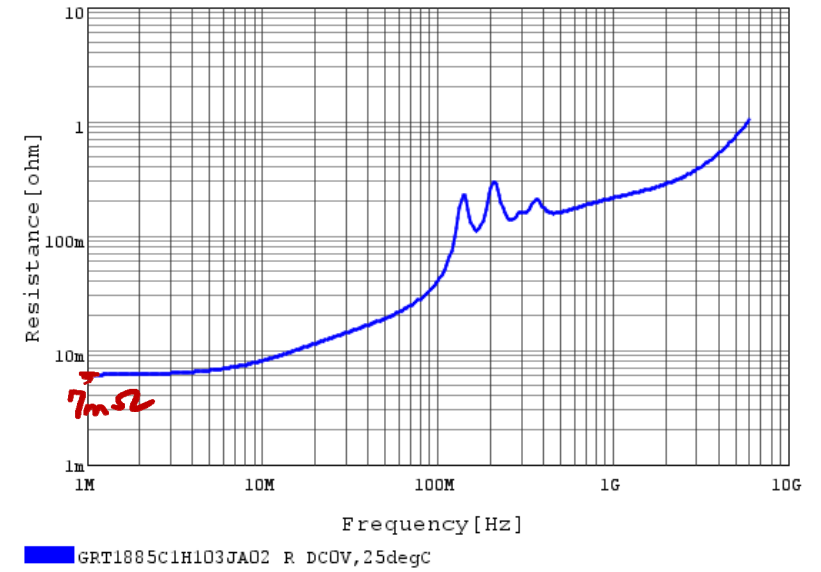
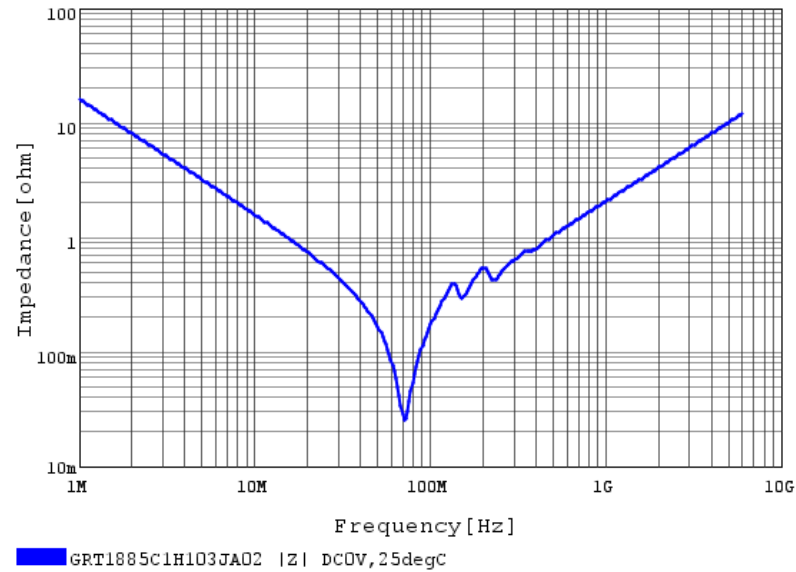
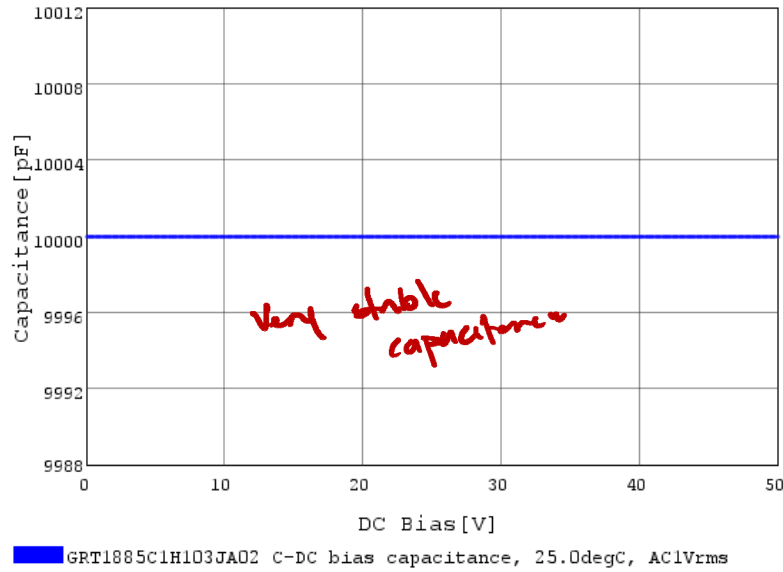
GRT188R61H225KE13 |Z| DCOV, 25degC



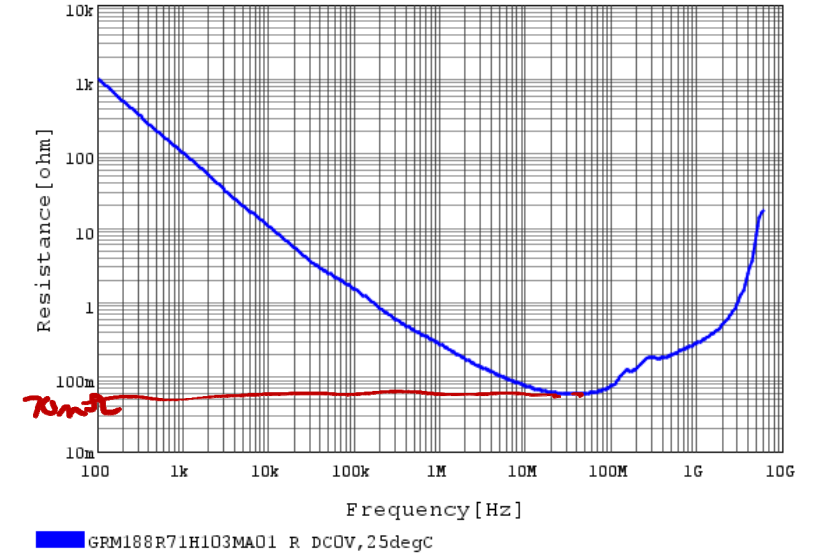
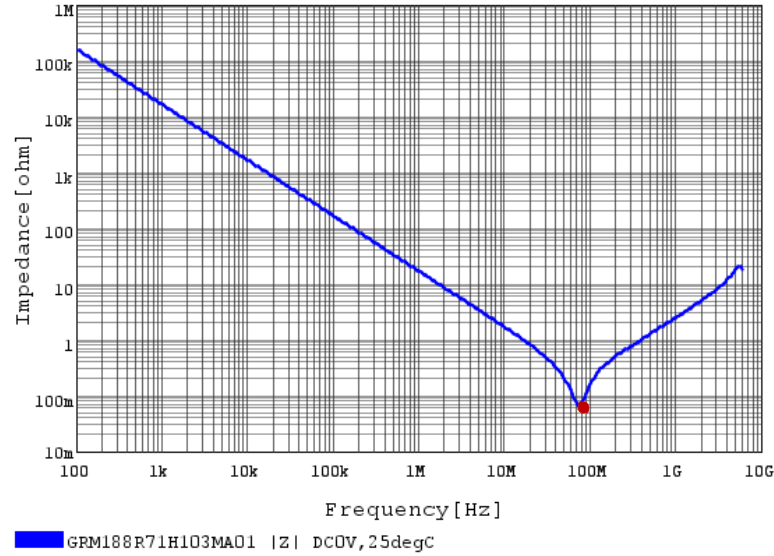
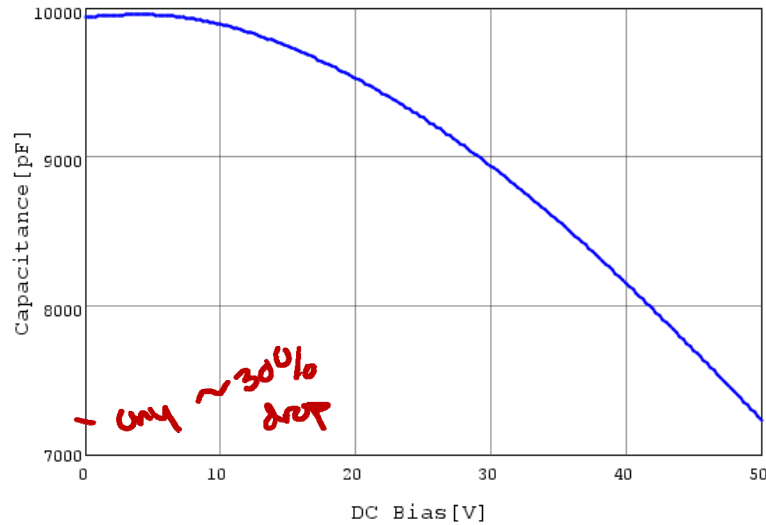
GRT188R61H225KE13 R DCOV, 25degC

Remaining: 7.2% at full voltage

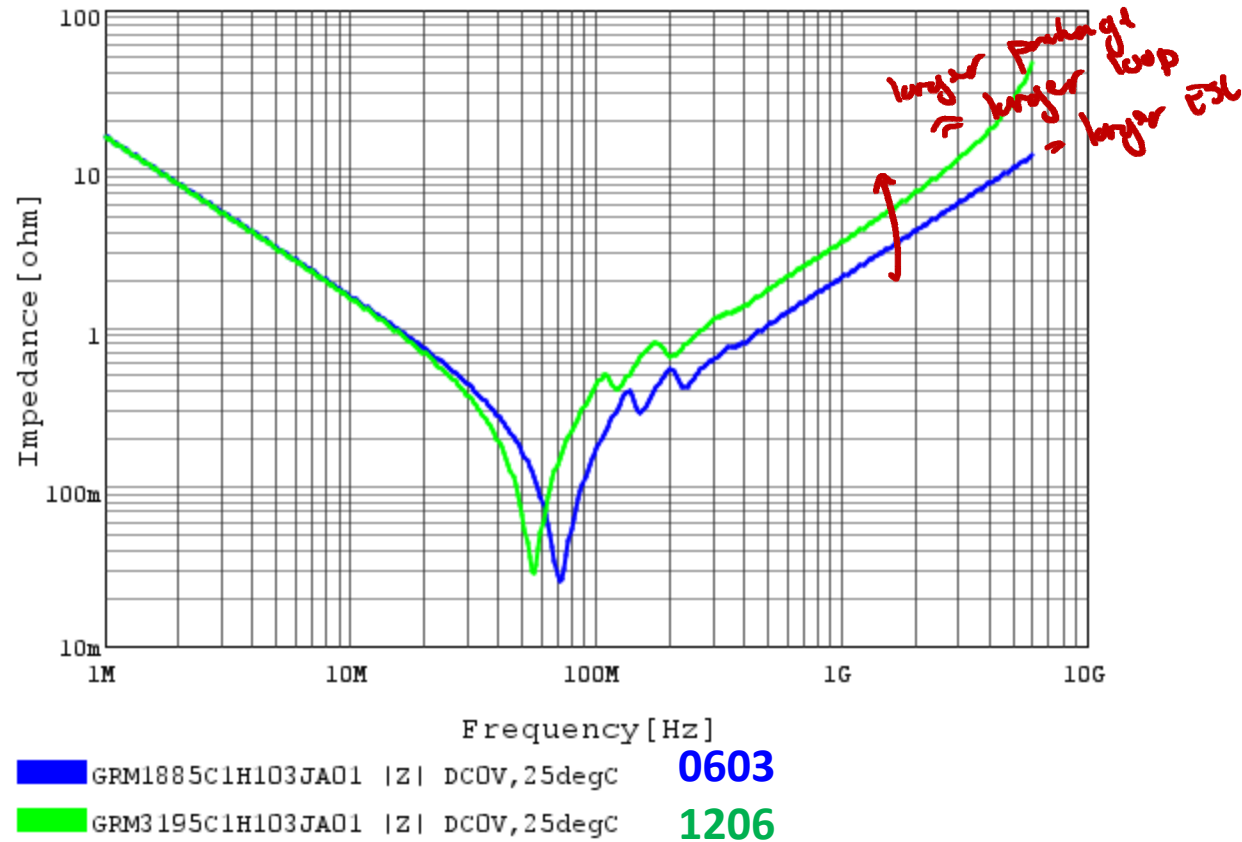
10nF, 50V C0G (Class-I) 0603 footprint



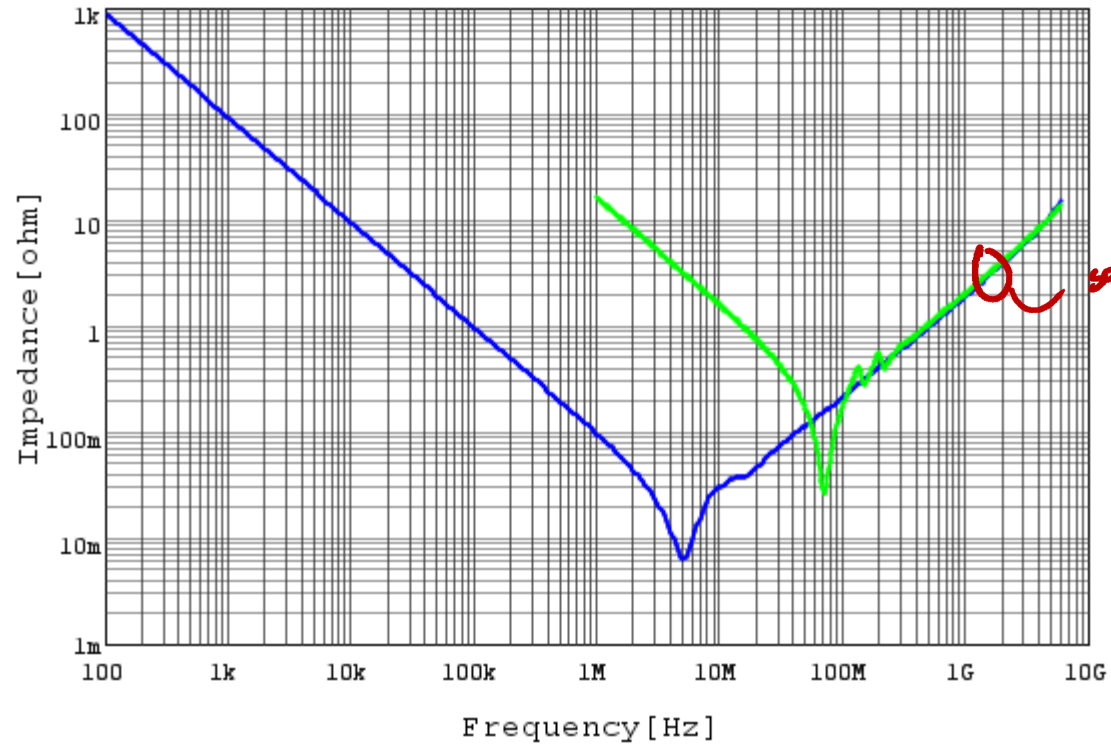
10nF, 50V X7R (Class-II) 0603 footprint



10nF, 50V C0G (Class-I) varied footprint

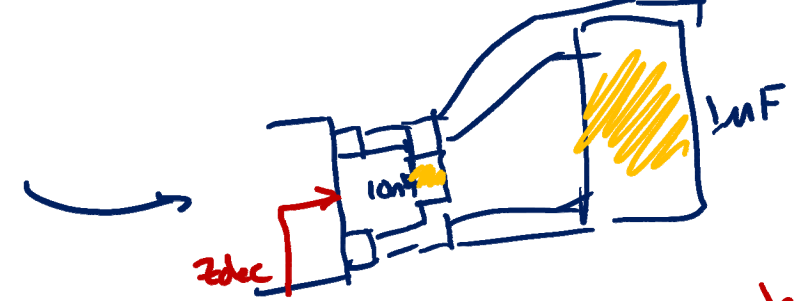
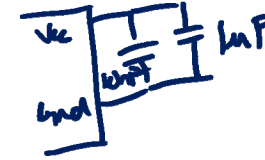


Same 0603 Footprint

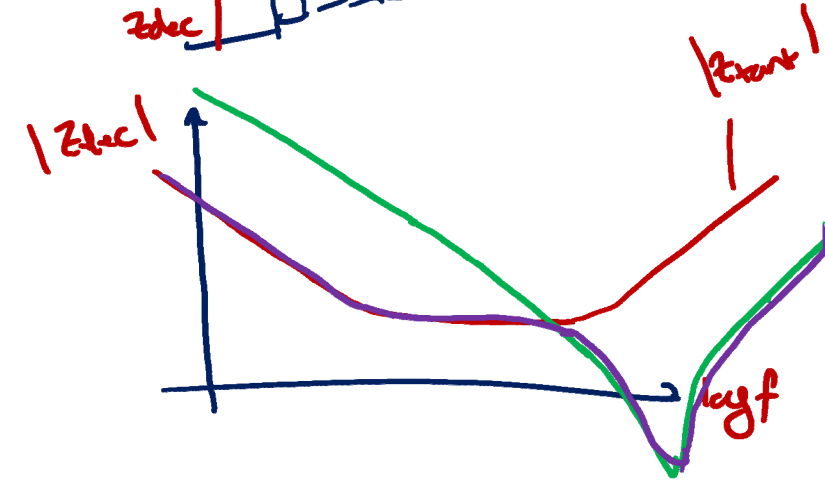
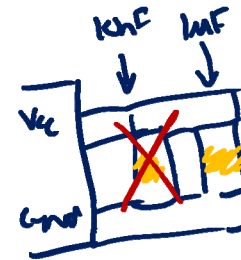


■ GRT188R61H225KE13 |Z| DCOV, 25degC **2.2µF X5R**
■ GCM1885C1H103GA16 |Z| DCOV, 25degC **10nF COG**

Common:



same ESL
(same package =
same loop)



Class-II Capacitor Hysteresis Loss

TABLE II
EMPLOYED COMPONENTS

Component	Dielectric	Manufacturer	Part Number	V_n	C_n	N(parallel)	C_{tot}	DF
C_{cal}	C0G	TDK	CAA572C0G2J204J640LH	650 V	200 nF	2	400 nF	< 0.02 %
C_{ref}	C0G	TDK	C5750C0G2A154J230KE	100 V	150 nF	32	4.8 μ F	< 0.03 %
C_{DUT}	X7R	Knowles Syfer	2220Y1K00474KETWS2	1 kV	470 nF	1	470 nF	> 0.71 %

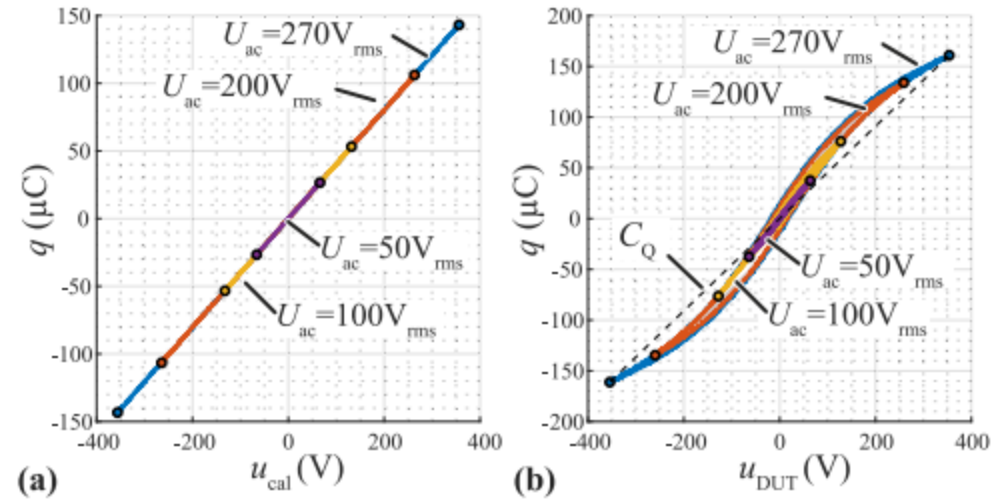


Fig. 6. $U - Q$ hysteresis recorded at 50 Hz for a range of excitation voltages for (a) the calibration capacitor, which shows no hysteresis and has a constant $C_Q = C_d$ at all voltages, and (b) the DUT, which exhibits increasing hysteresis and losses with increasing excitation voltage. C_Q highlighted for $U_{ac} = 270 V_{rms}$. Measured $U - Q$ curves are identical at 50 Hz and 100 Hz.

C_{oss} Hysteresis

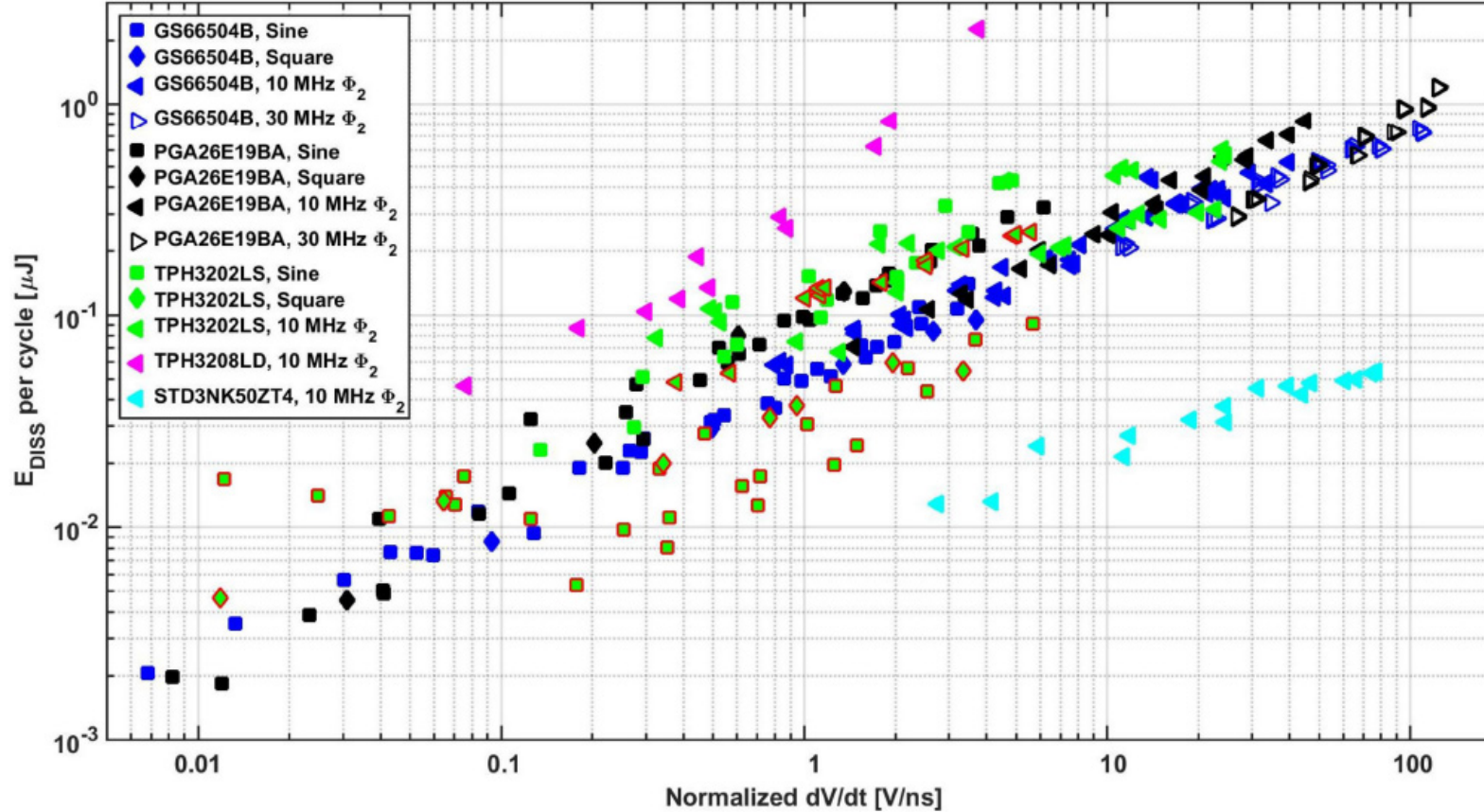


Fig. 15. Losses per cycle versus normalized, by (8), dV/dt for the three studied devices and two additional “extreme performance” devices. The red outline around the TPH3202LS results indicates applied voltages under 300 V and $\beta = 1.46$ in (8). All recorded measurements are included here. There are no measurements for the TPH3202LS 30 MHz Φ_2 , as the Φ_2 wave generator could not be tuned to maintain ZVS with the TPH3202LS device and C_{REF} in parallel.

Transistor Structure and Material

SiC

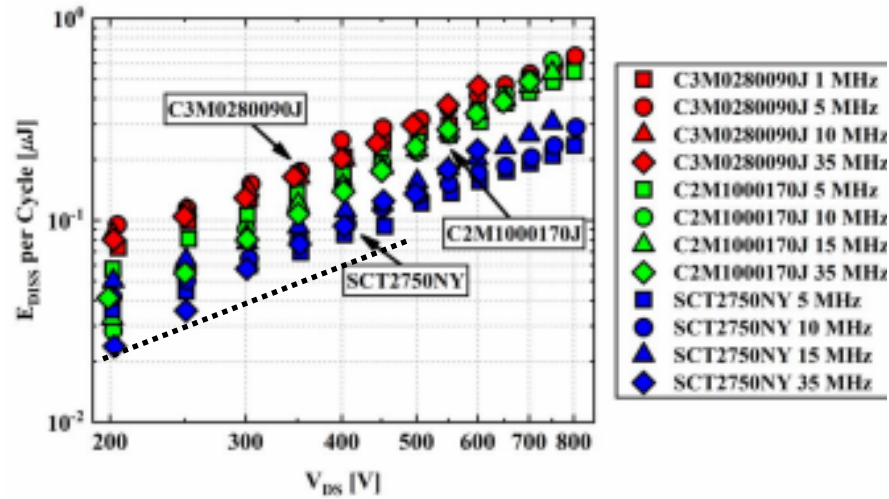
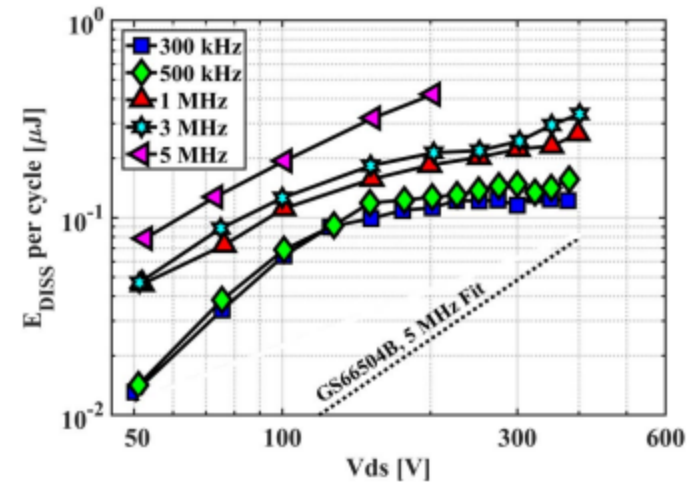


Fig. 4: C_{OSS} losses for three devices from 1-35 MHz.

Si Superjunction



(b) High-frequency C_{OSS} losses for the R6011KNTJL device.

Fig. 6: Silicon superjunction C_{OSS} loss data.

Si

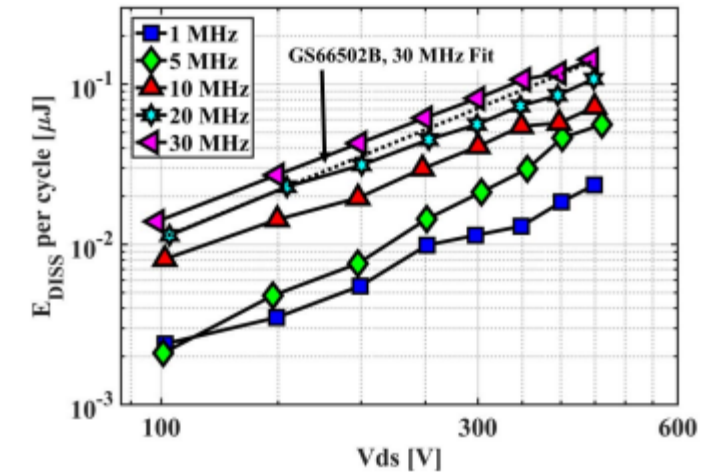


Fig. 7: C_{OSS} losses for STD3NK50ZT4.

Inductor Design

Tiny Box Comments

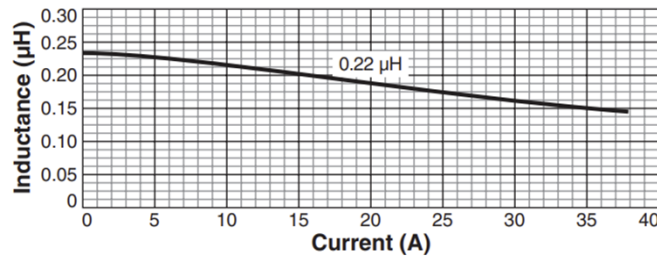
- Many nonlinear and complex loss phenomena in magnetics
- Online tools from manufacturers are usually poor predictors of performance with large, high-frequency ripple

POL Inductors

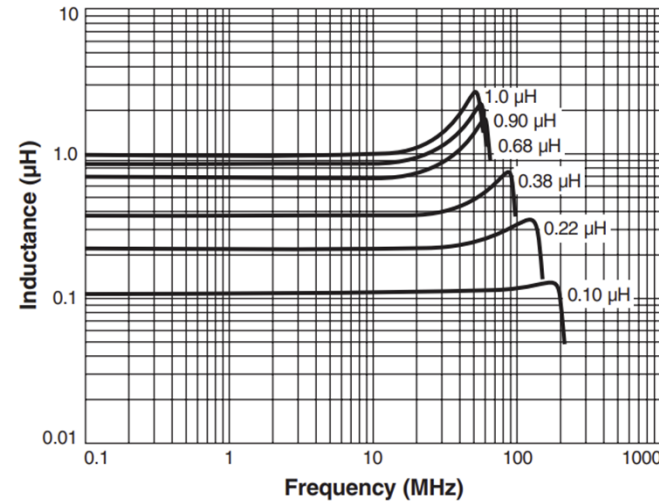


e.g. Coilcraft XEL5020

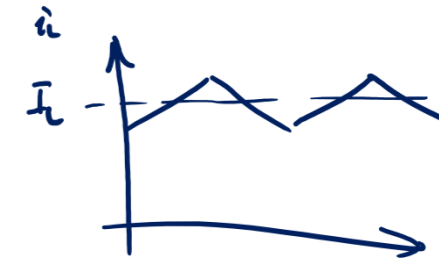
- $0.68\mu\text{H}$, $8.9\text{m}\Omega$ DCR
- $P_{DC} = 890\text{mW}$
- 12Arms for 40°C temp rise



L vs Frequency



Part number ¹	Inductance ² ±20% (μH)	DCR (mOhms) ³		SRF typ ⁴ (MHz)	Isat ⁵ (A)	Irms (A) ⁶	
		typ	max			20°C rise	40°C rise
XEL5020-101ME_	0.10	1.90	2.20	209	39.0	19.0	25.0
XEL5020-221ME_	0.22	3.50	4.05	129	28.0	17.0	21.0
XEL5020-381ME_	0.38	4.80	5.50	89	22.0	12.0	15.0
XEL5020-681ME_	0.68	8.90	10.25	65	16.3	8.6	12.0
XEL5020-901ME_	0.90	10.90	12.53	57	13.9	8.4	10.0
XEL5020-102ME_	1.0	12.60	14.50	53	12.4	7.4	9.6

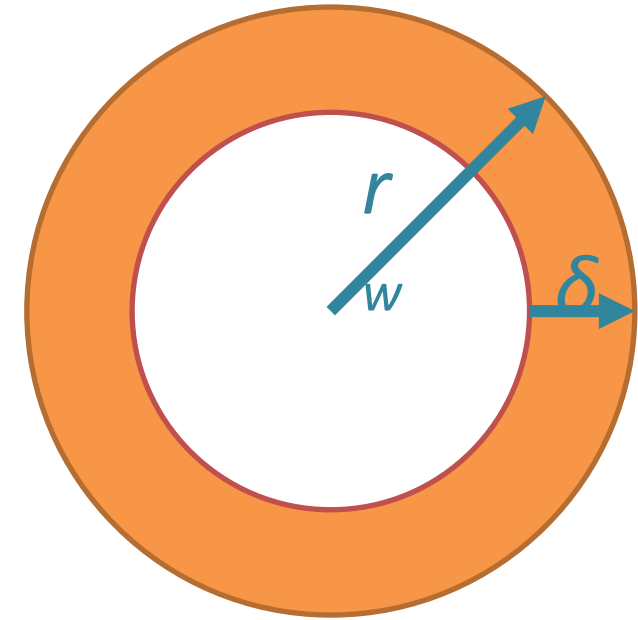
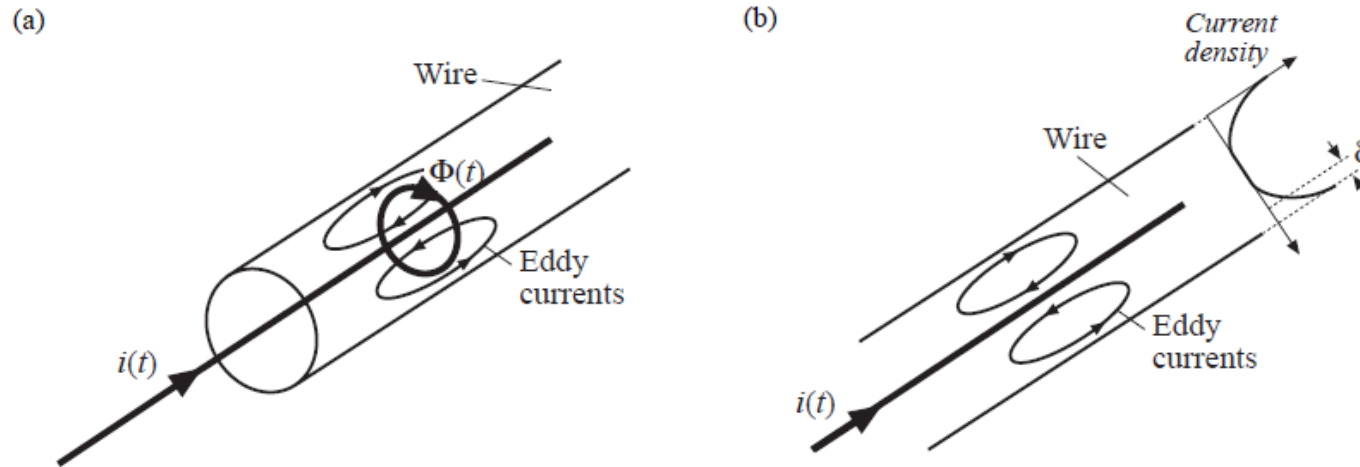


XEL5020-681

Inductor losses and temperature rise
at 1 MHz, 10 A IDC, 10 A ΔIL

Total losses	4251 mW
DCR typ. loss	890 mW
Core + AC winding loss	3361 mW
Temperature rise at 25°C ambient	133 °C

Skin Effect in Copper Wire



- Current profile at high frequency is exponential function of distance from center with characteristic length δ

$$A_{w,eff} = \pi r_w^2 - \pi(r_w - \delta)^2$$

$$R_{ac} = \rho \frac{l_b}{A_{w,eff}}$$

Skin Depth

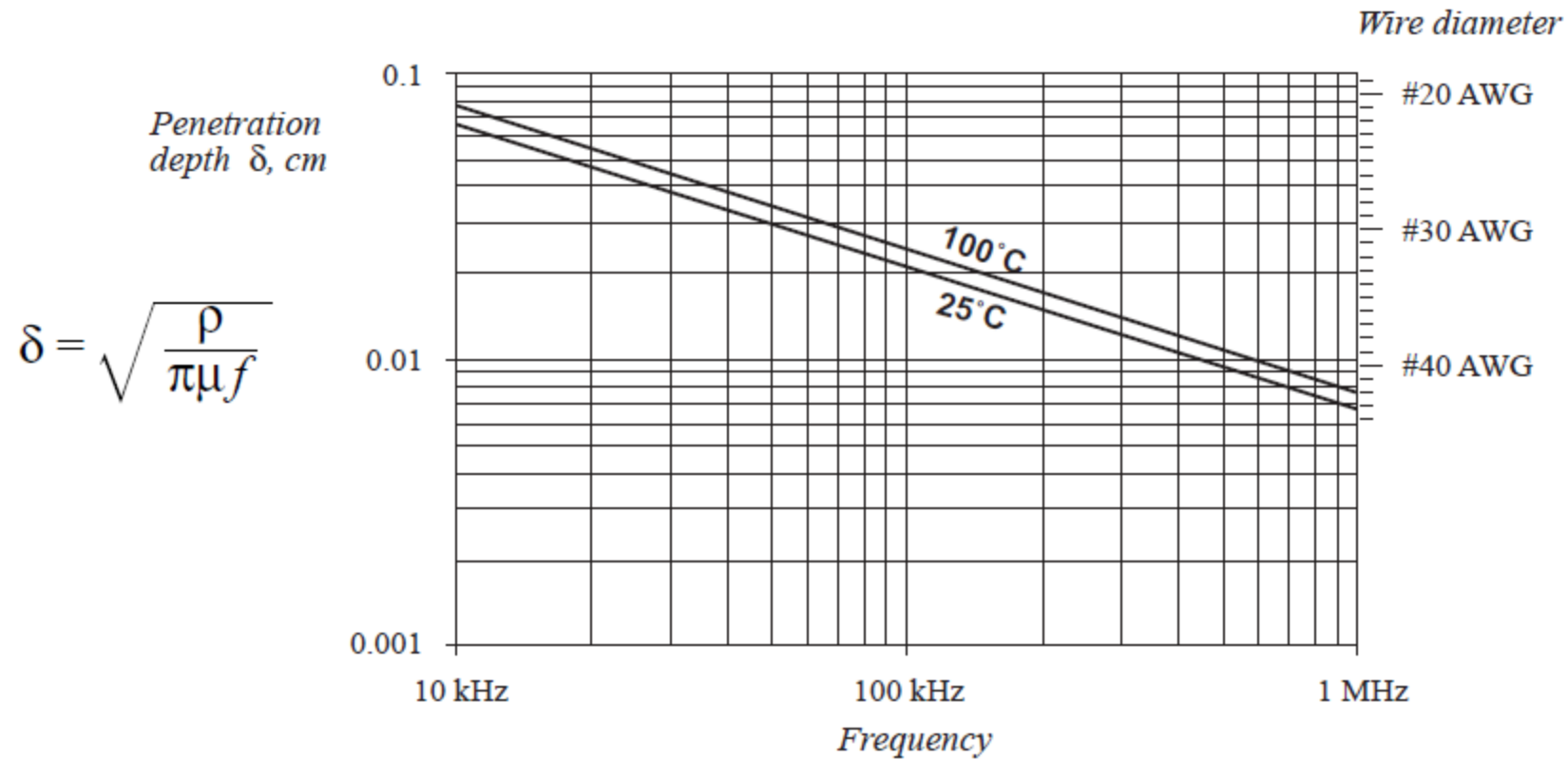
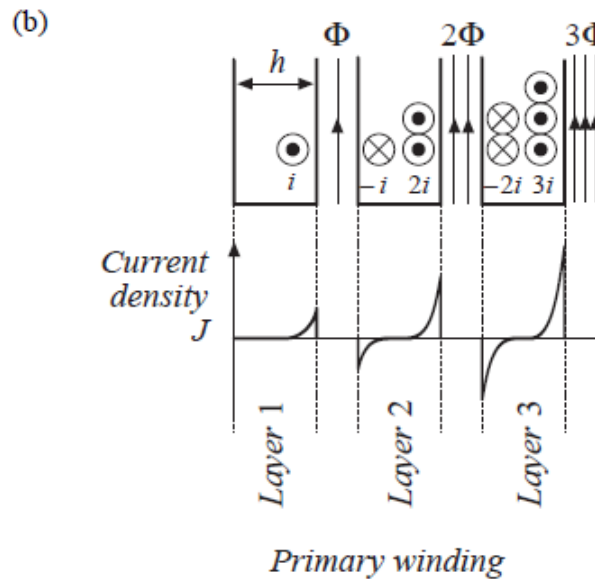
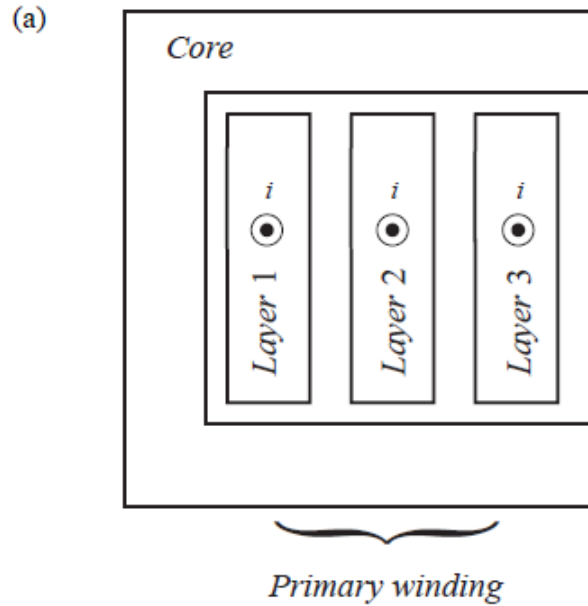


Fig. 13.23 Penetration depth δ , as a function of frequency f , for copper wire.

Proximity Effect



- In *foil* conductor closely spaced with $h \gg \delta$, flux between layers generates additional current according to Lenz's law.

$$P_1 = I_{L,rms}^2 R_{ac}$$

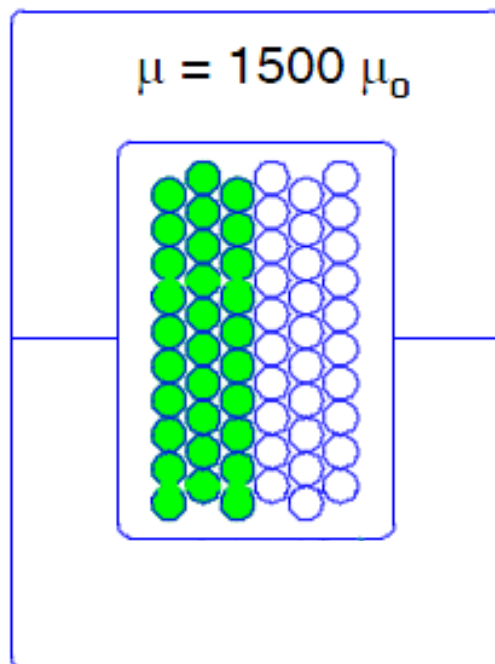
- Power loss in layer 2:

$$P_2 = I_{L,rms}^2 R_{ac} + (2I_{L,rms})^2 R_{ac}$$

$$P_2 = 5P_1$$

- Needs modification for non-foil conductors

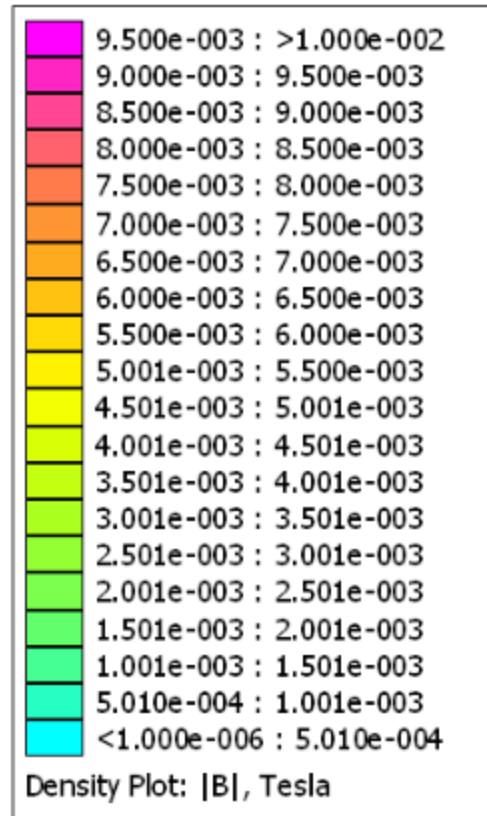
Simulation Example



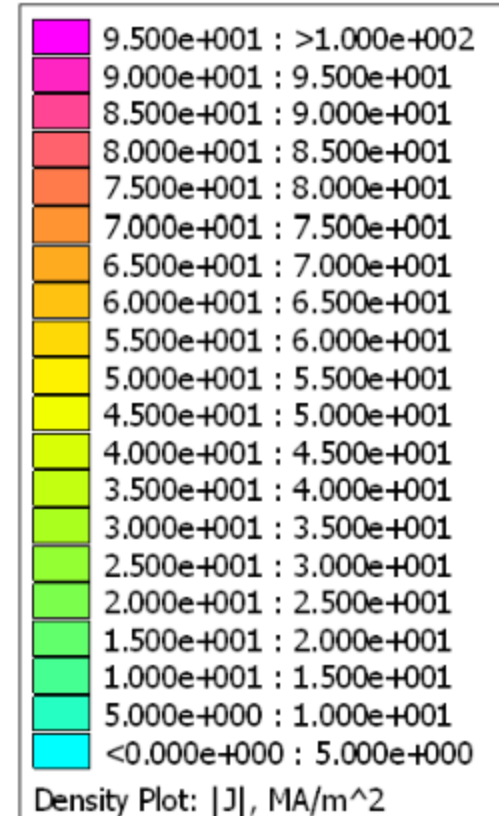
- AWG#30 copper wire
 - Diameter $d = 0.294$ mm
 - $d = \delta$ at around 50 kHz
- 1:1 transformer
 - Primary and secondary are the same, 30 turns in 3 layers
- Sinusoidal currents,
 $I_{1rms} = I_{2rms} = 1$ A

Numerical field and current density solutions using FEMM (Finite Element Method Magnetics), a free 2D solver, <http://www.femm.info/wiki/HomePage>

Flux density magnitude

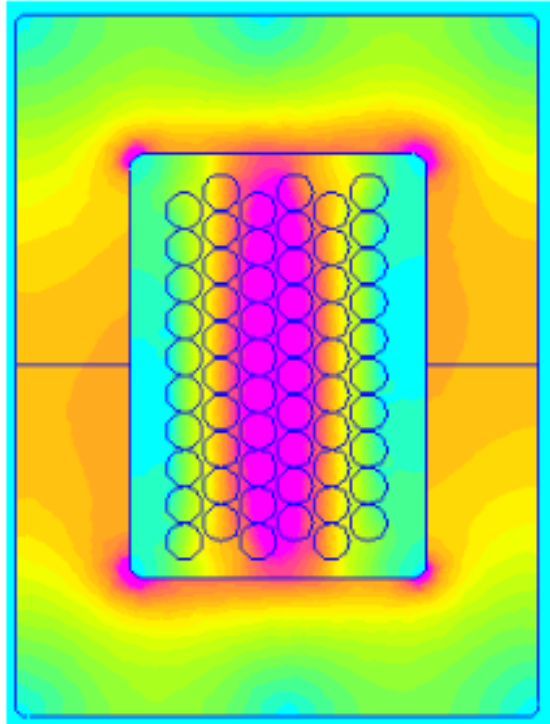


Current density magnitude

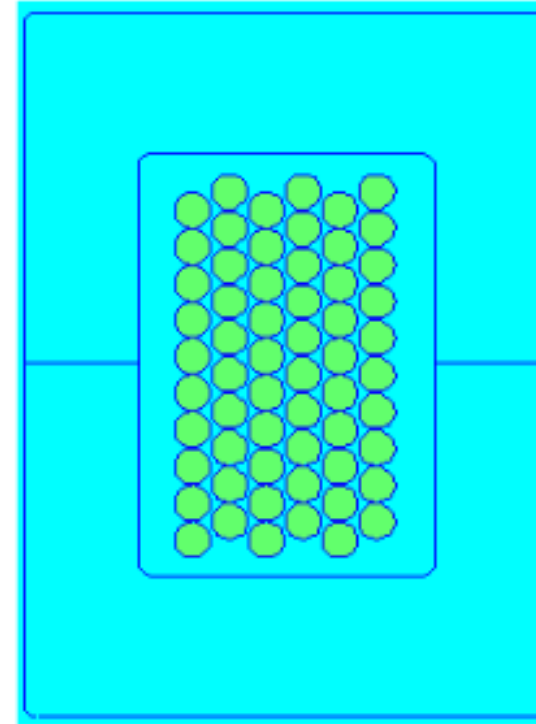


Frequency: 1 kHz

Flux density

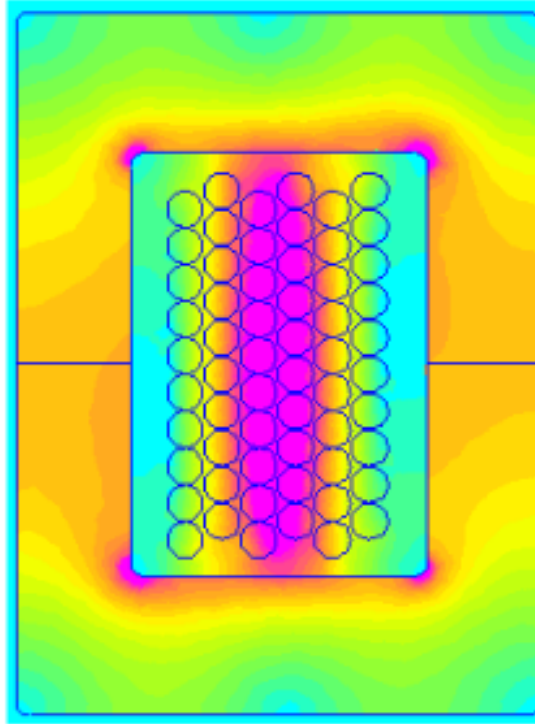


Current Density

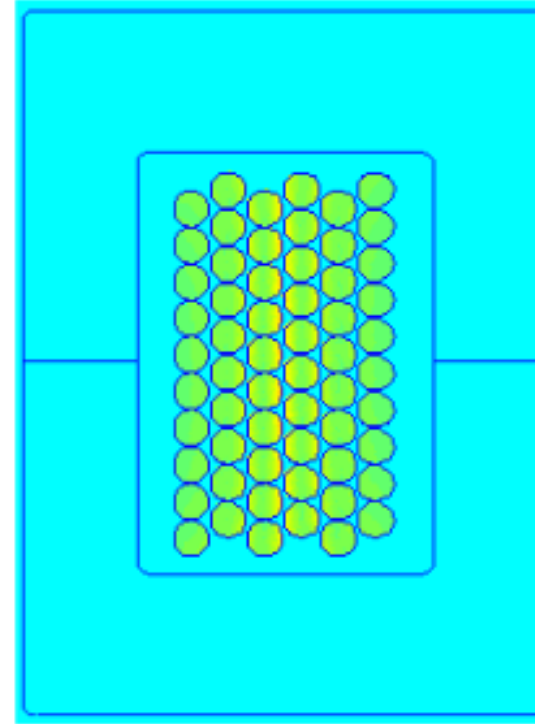


Frequency: 100 kHz

Flux density



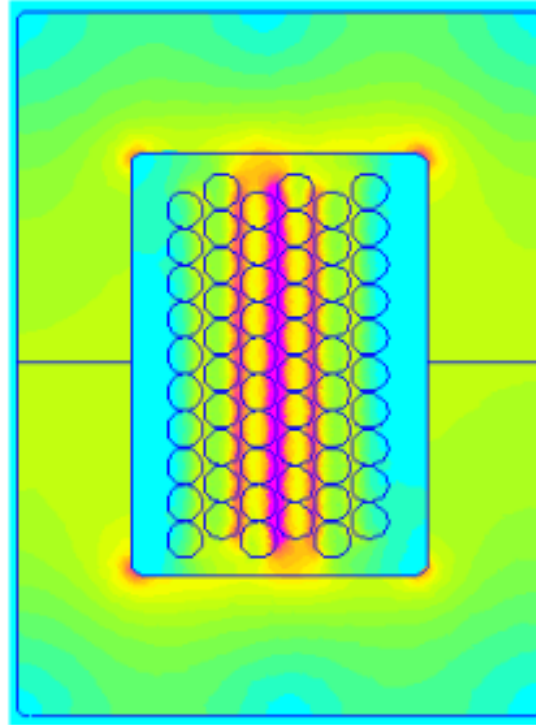
Current Density



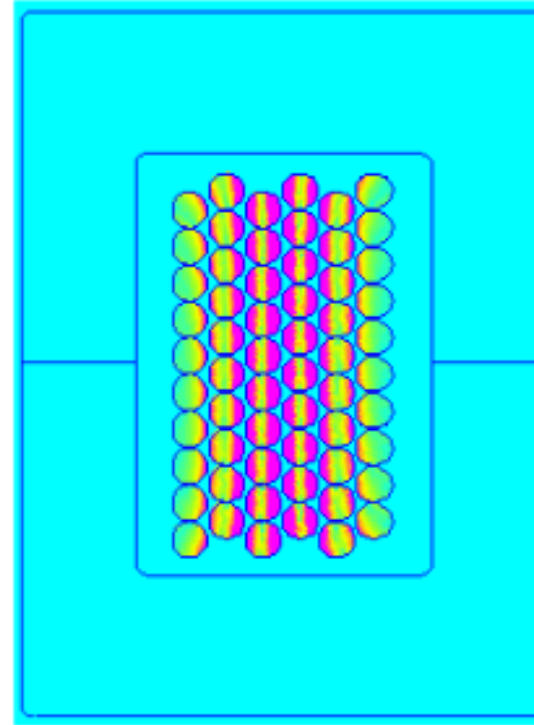
Total copper losses 1.8 larger than at 1 kHz

Frequency: 1 MHz

Flux density



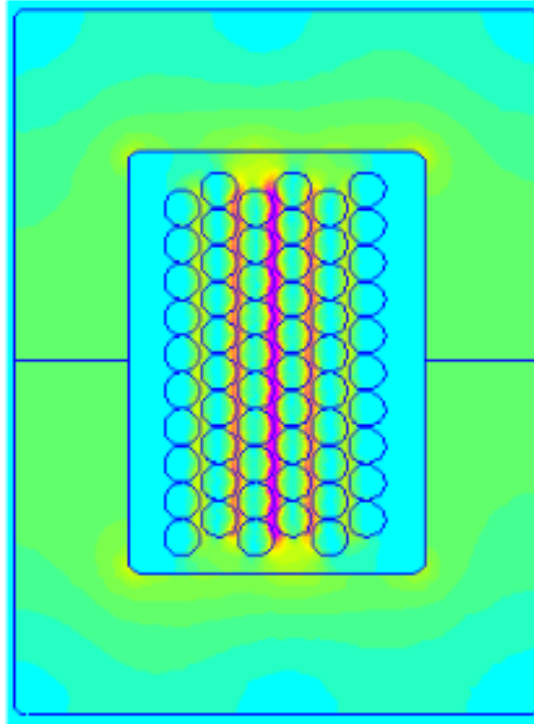
Current Density



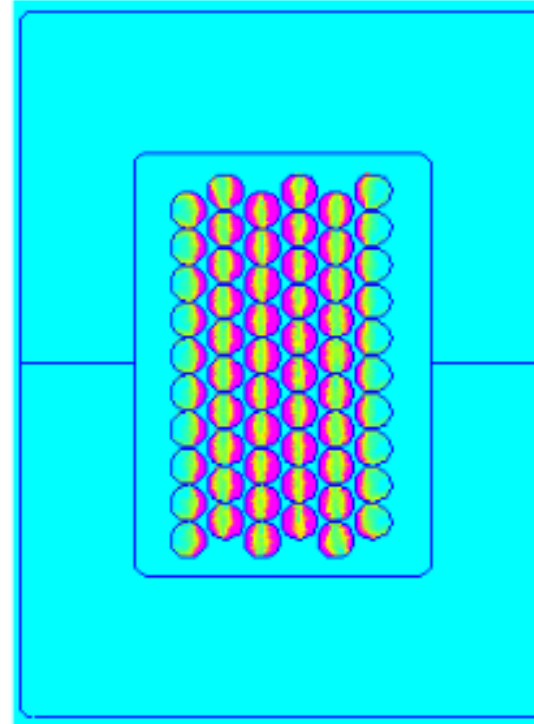
Total copper losses 20 times larger than at 1 kHz

Frequency: 10 MHz

Flux density



Current Density

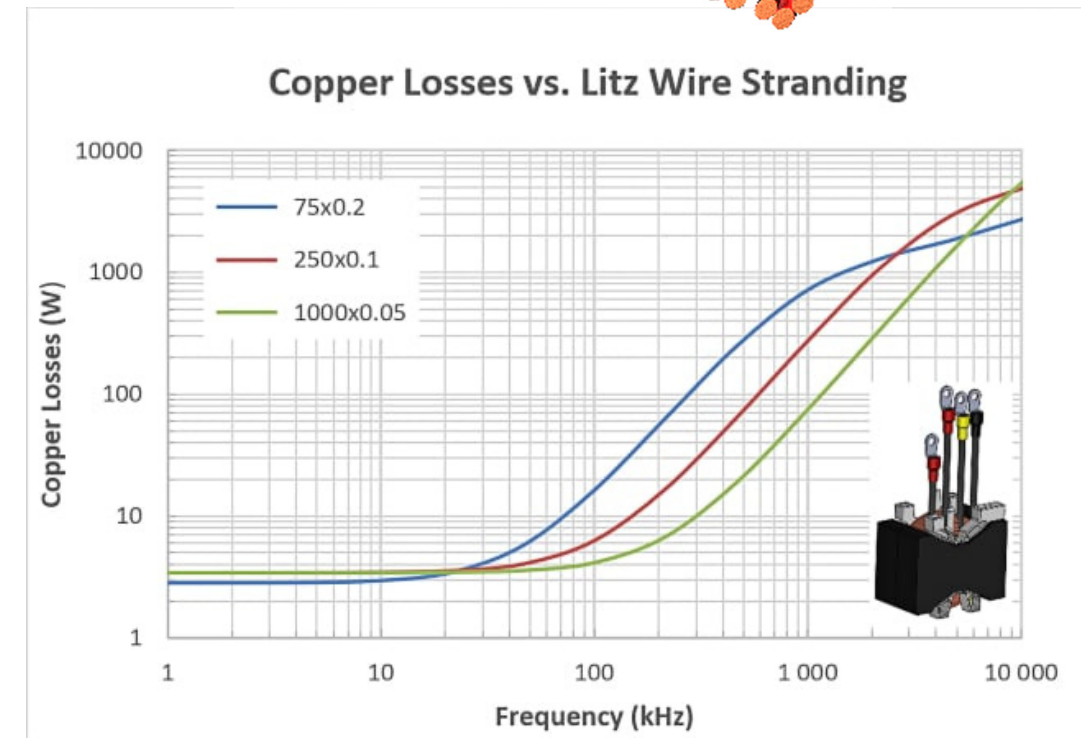
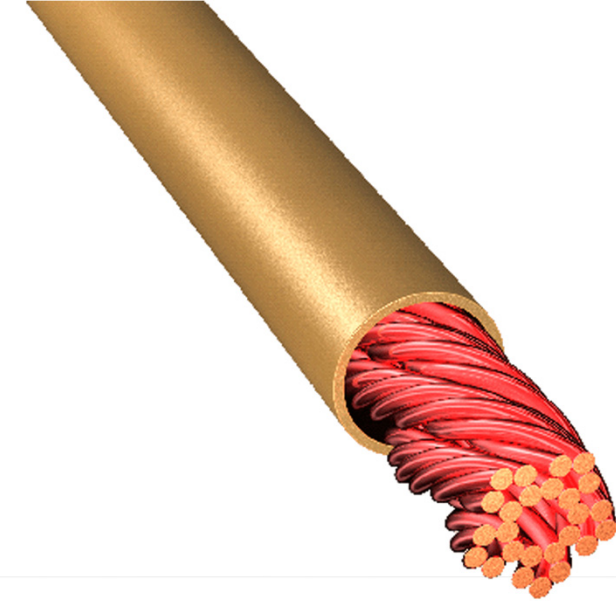
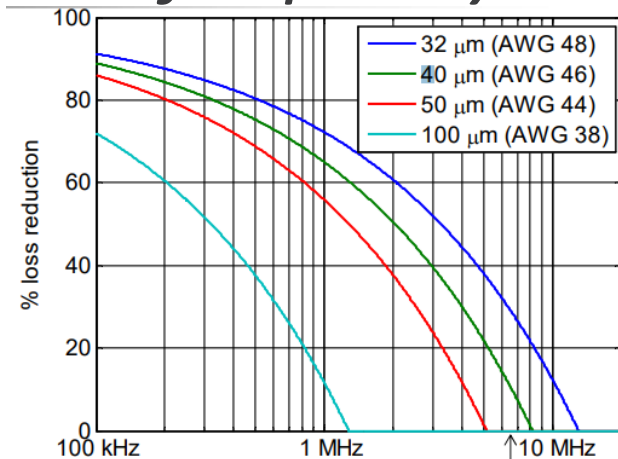


Very significant proximity effect

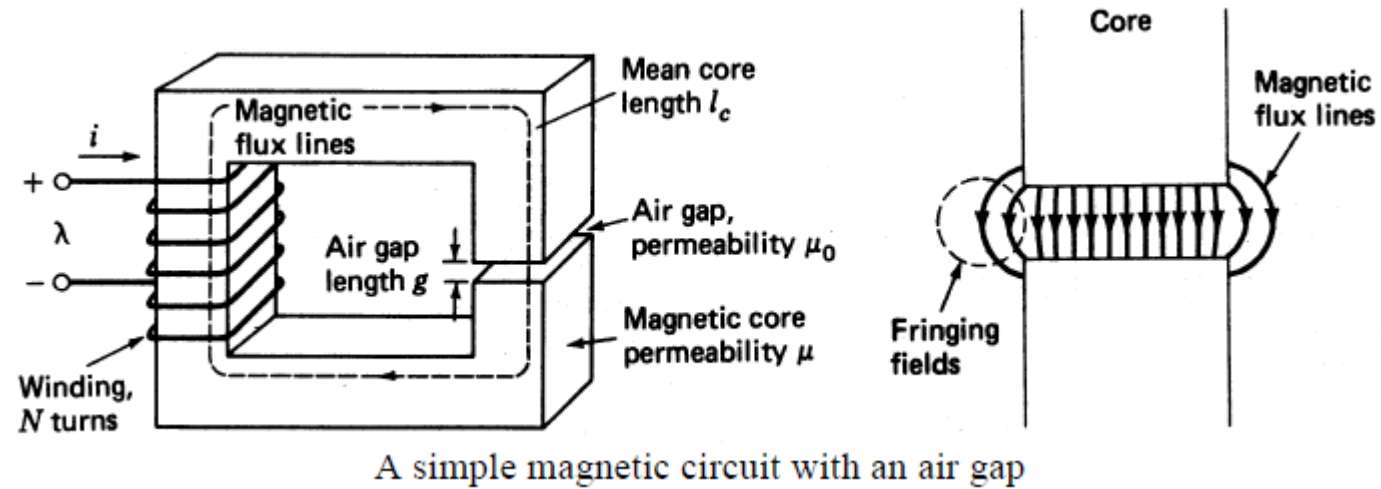
Total copper losses = 65 times larger than at 1 KHz

Litz Wire

- Braided, insulated strands with $d \ll \delta$
- Now has strand/bundle/wire level ac resistance effects
- Significantly lower resistance *in a bounded frequency range*



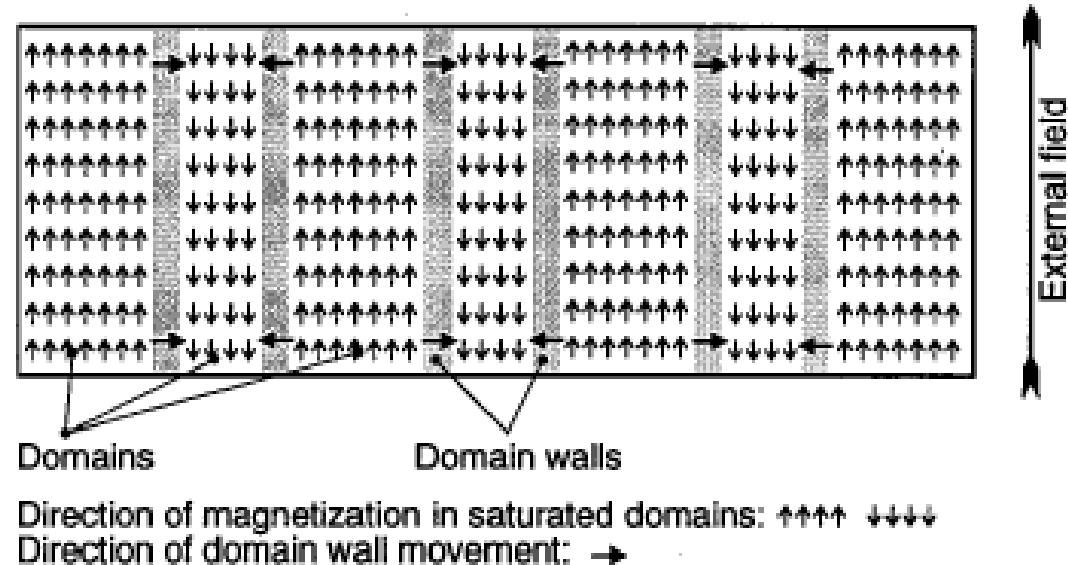
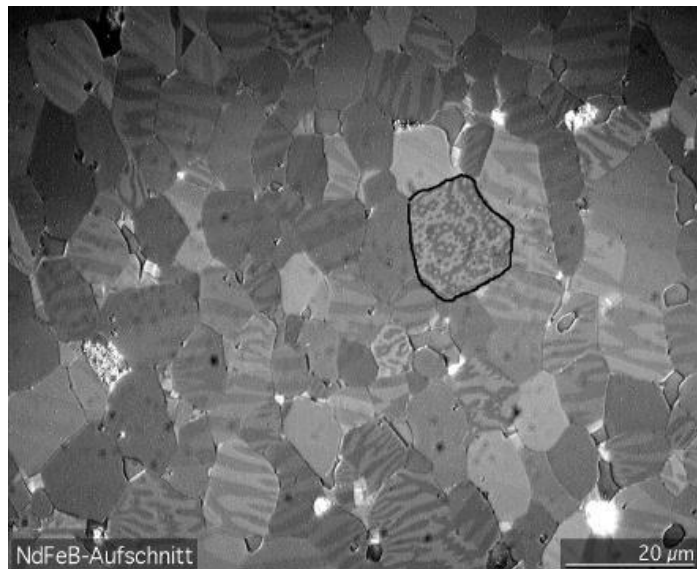
Fringing



- Near air gap, flux may bow out significantly, causing additional eddy current losses in nearby conductors

Physical Origin of Core Loss

- Magnetic material is divided into “domains” of saturated material
- Both Hysteresis and Eddy Current losses occur from domain wall shifting



Inductor Core Loss

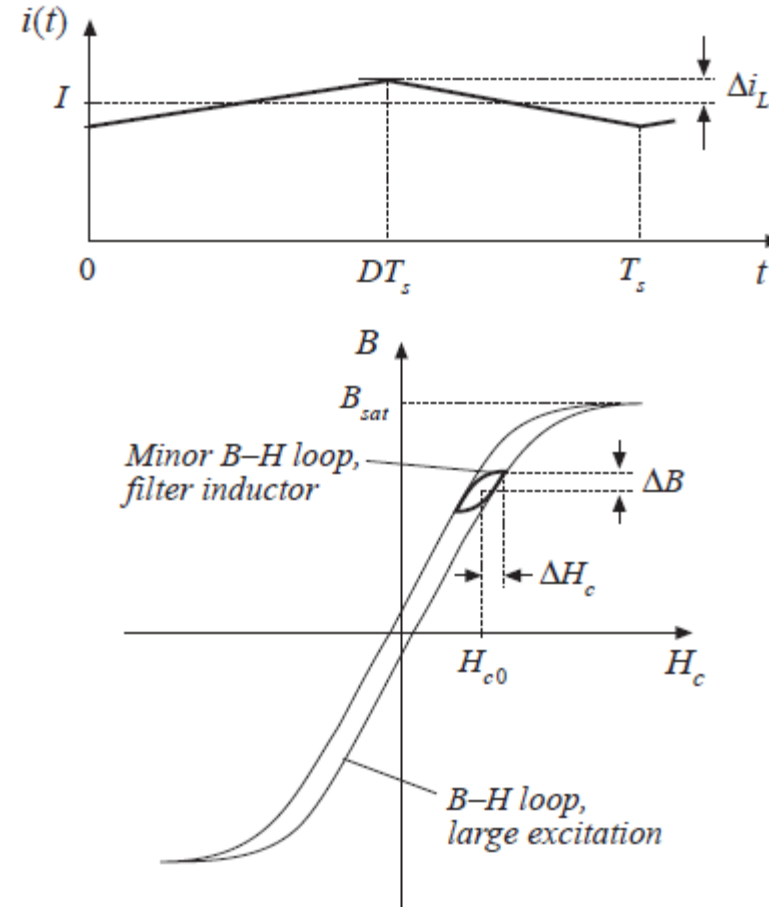
- Governed by Steinmetz Equation:

$$P_v = K_{fe} f_s^\alpha (\Delta B)^\beta \quad [\text{mW/cm}^3]$$

- Parameters K_{fe} , α , and β extracted from manufacturer data

$$P_{fe} = P_v A_c l_m \quad [\text{mW}]$$

- $\Delta B \propto \Delta i_L \rightarrow$ small losses with small ripple



Steinmetz Parameter Extraction

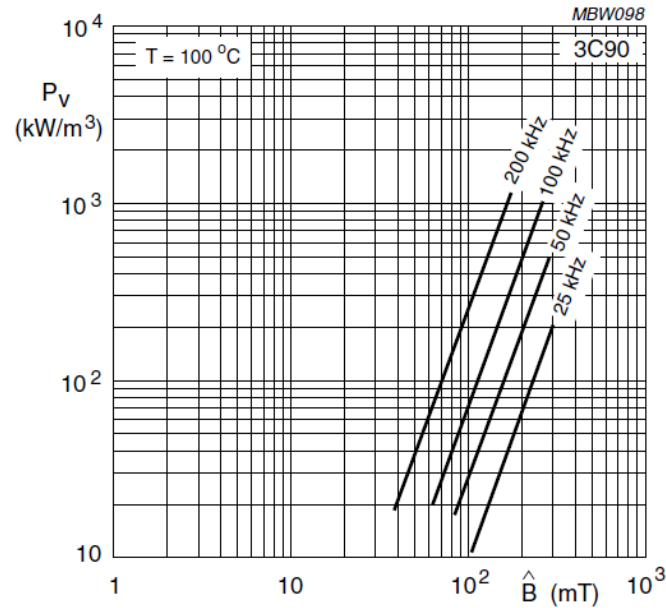


Fig.6 Specific power loss as a function of peak flux density with frequency as a parameter.

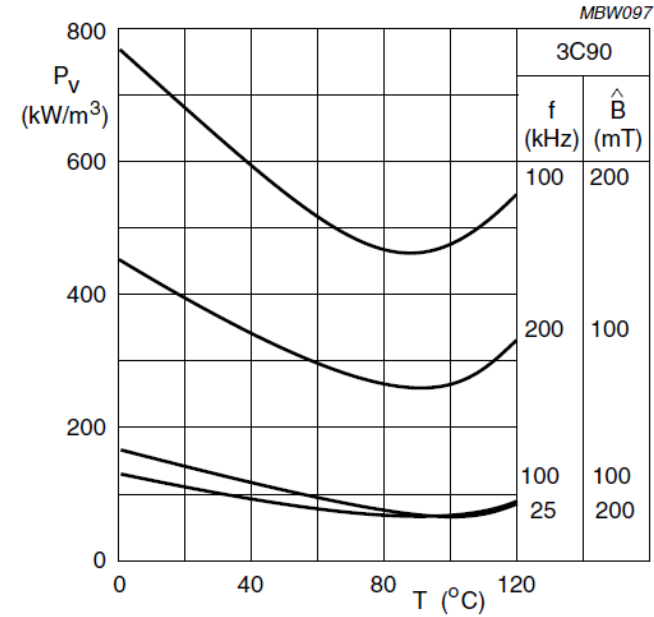


Fig.7 Specific power loss for several frequency/flux density combinations as a function of temperature.

Ferroxcube Curve Fit Parameters

Power losses in our ferrites have been measured as a function of frequency (f in Hz), peak flux density (B in T) and temperature (T in °C). Core loss density can be approximated ⁽²⁾ by the following formula :

$$P_{core} = C_m \cdot f^x \cdot B_{peak}^y (ct_0 - ct_1 T + ct_2 T^2) \quad [3]$$

$$= C_m \cdot C_T \cdot f^x \cdot B_{peak}^y \quad [\text{mW/cm}^3]$$

ferrite	f (kHz)	C _m	x	y	ct ₂	ct ₁	ct ₀
3C30	20-100	7.13.10 ⁻³	1.42	3.02	3.65.10 ⁻⁴	6.65.10 ⁻²	4
	100-200	7.13.10 ⁻³	1.42	3.02	4.10 ⁻⁴	6.8 .10 ⁻²	3.8
3C90	20-200	3.2.10 ⁻³	1.46	2.75	1.65.10 ⁻⁴	3.1.10 ⁻²	2.45
3C94	20-200	2.37.10 ⁻³	1.46	2.75	1.65.10 ⁻⁴	3.1.10 ⁻²	2.45
	200-400	2.10 ⁻⁹	2.6	2.75	1.65.10 ⁻⁴	3.1.10 ⁻²	2.45
3F3	100-300	0.25.10 ⁻³	1.63	2.45	0.79.10 ⁻⁴	1.05.10 ⁻²	1.26
	300-500	2.10 ⁻⁵	1.8	2.5	0.77.10 ⁻⁴	1.05.10 ⁻²	1.28
	500-1000	3.6.10 ⁻⁹	2.4	2.25	0.67.10 ⁻⁴	0.81.10 ⁻²	1.14
3F4	500-1000	12.10 ⁻⁴	1.75	2.9	0.95.10 ⁻⁴	1.1.10 ⁻²	1.15
	1000-3000	1.1.10 ⁻¹¹	2.8	2.4	0.34.10 ⁻⁴	0.01.10 ⁻²	0.67

Table 1: Fit parameters to calculate the power loss density

NSE/iGSE

$$P_{NSE} = \left(\frac{\Delta B}{2} \right)^{\beta-\alpha} \frac{k_N}{T} \int_0^T \left| \frac{dB}{dt} \right|^\alpha dt$$

$$k_N = \frac{k}{(2\pi)^{\alpha-1} \int_0^{2\pi} |\cos \theta|^\alpha d\theta}$$

Simple Formula for Square-wave voltages:

$$P_{NSE} = k_N (2f)^\alpha (\Delta B)^\beta (D^{1-\alpha} + (1-D)^{1-\alpha}) \quad (10)$$

where f is the operating frequency;
 $\Delta B / 2$ is the peak induction;
 D is the duty ratio of the square wave voltage.

Note: The second and third harmonics are dominant at moderate values of duty ratio D . For extreme values of D (95%), a higher value of α could give better matching to the actual losses.

